





PNP SURFACE MOUNT TRANSIS

Features

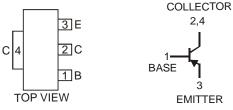
- **Epitaxial Planar Die Construction**
- Complementary NPN Type Available (DXTA42)
- Ideally Suited for Automated Assembly Processes
- Ideal for Medium Power Switching or Amplification Applications
- Lead Free By Design/RoHS Compliant (Note 1)
- "Green" Device (Note 2)



SOT89-3L

Mechanical Data

- Case: SOT89-3L
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Finish Matte Tin annealed over Copper leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208
- Marking & Type Code Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.072 grams (approximate)



Schematic and Pin Configuration

Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-300	V
Collector-Emitter Voltage	V _{CEO}	-300	V
Emitter-Base Voltage	V _{EBO}	-5	V
Continuous Collector Current	Ic	-500	mA

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 3) @ T _A = 25°C	P _D	1	W
Thermal Resistance, Junction to Ambient (Note 3)	$R_{ heta JA}$	125	°C/W
Operating and Storage Temperature Range	T _j , T _{STG}	-55 to +150	°C

Electrical Characteristics @TA = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Conditions
OFF CHARACTERISTICS (Note 4)						
Collector-Base Breakdown Voltage	V _{(BR)CBO}	-300		_	V	$I_C = -100 \mu A, I_E = 0$
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	-300			V	$I_C = -1 \text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5	_		V	$I_E = -100 \mu A, I_C = 0$
Collector-Base Cut-off Current	I _{CBO}		_	-0.25	μΑ	V _{CB} = -200V, I _E = 0
Emitter-Base Cut-off Current	I _{EBO}	_	_	-0.1	μΑ	$V_{EB} = -3V, I_{C} = 0A$
ON CHARACTERISTICS (Note 4)						
Collector-Emitter Saturation Voltage	V _{CE(SAT)}		_	-0.5	V	$I_C = -20 \text{mA}, I_B = -2 \text{mA}$
Base-Emitter Saturation Voltage	V _{BE(SAT)}		_	-0.9	V	$I_C = -20 \text{mA}, I_B = -2 \text{mA}$
		25	_	_		$I_C = -1 \text{mA}, V_{CE} = -10 \text{V}$
Static Forward Current Transfer Ratio	hFE	40	_		V	$I_C = -10 \text{mA}, V_{CE} = -10 \text{V}$
		25	_	_		$I_C = -30 \text{mA}, V_{CE} = -10 \text{V}$
SMALL SIGNAL CHARACTERISTICS						
Gain-Bandwidth Product	f⊤	50	_		MHz	$I_C = -10 \text{mA}, V_{CE} = -20 \text{V},$ f = 100MHz
Output Capacitance	C_{obo}		_	6	pF	V _{CB} = -20V, f = 1MHz

Notes:

- No purposefully added lead.
- Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
- Device mounted on FR-4 PCB; pad layout as shown on page 4 or in Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.
- 4. Measured under pulsed conditions. Pulse width = 300μs. Duty cycle ≤2%.



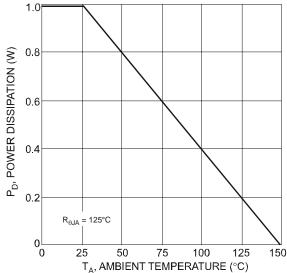


Fig. 1, Power Dissipation vs. Ambient Temperature (Note 3)

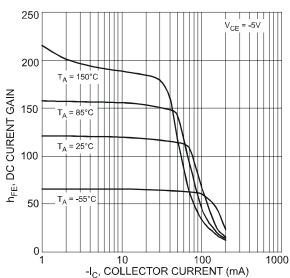


Fig. 3, Typical DC Current Gain vs. Collector Current

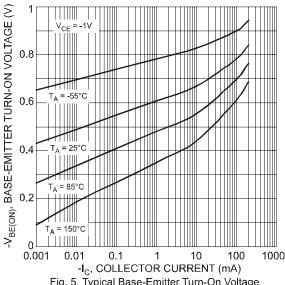
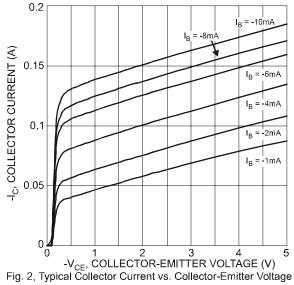


Fig. 5, Typical Base-Emitter Turn-On Voltage vs. Collector Current



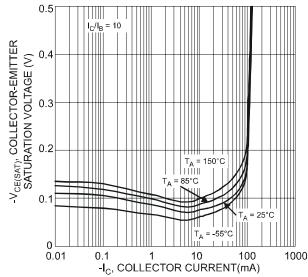


Fig. 4, Typical Collector-Emitter Saturation Voltage vs. Collector Current

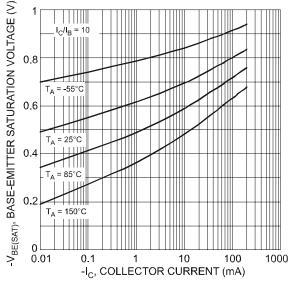
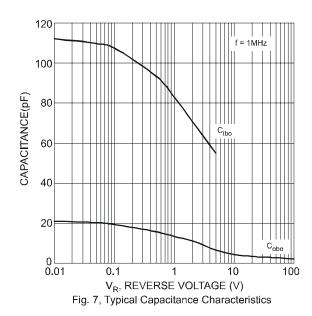


Fig. 6, Typical Base-Emitter Saturation Voltage vs. Collector Current





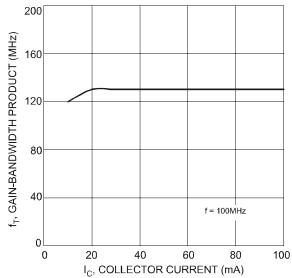


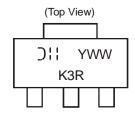
Fig. 8, Typical Gain-Bandwidth Product vs. Collector Current

Ordering Information (Note 5)

Device	Packaging	Shipping
DXTA92-13	SOT89-3L	2500/Tape & Reel

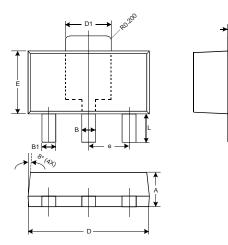
5. For packaging details, go to our website at http://www.diodes.com/ap02007.pdf.

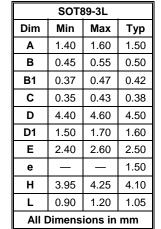
Marking Information



☐ = Manufacturer's Code Marking K3R = Product Type Marking Code YWW = Date Code Marking Y = Last digit of year ex: 7 = 2007 WW = Week code 01 - 52

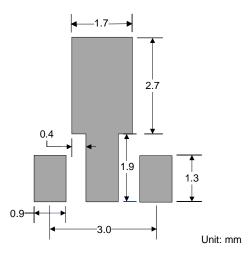
Package Outline Dimensions







Suggested Pad Layout



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